



FCU4300N80Z

N-Channel SuperFET® II MOSFET

800 V, 1.6 A, 4.3 Ω

Features

- $R_{DS(on)} = 3.4 \Omega$ (Typ.)
- Ultra Low Gate Charge (Typ. $Q_g = 6.8 \text{ nC}$)
- Low E_{oss} (Typ. 0.8 μJ @ 400V)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 36 \text{ pF}$)
- 100% Avalanche Tested
- RoHS Compliant
- ESD Improved Capability

Applications

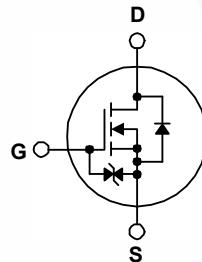
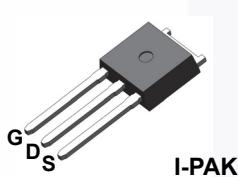
- AC - DC Power Supply
- LED Lighting

December 2014



Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. In addition, internal gate-source ESD diode allows to withstand over 2kV HBM surge stress. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as Audio, Laptop adapter, Lighting, ATX power and industrial power applications.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter		FCU4300N80Z	Unit
V_{DSS}	Drain to Source Voltage		800	V
V_{GSS}	Gate to Source Voltage	- DC	± 20	V
		- AC ($f > 1 \text{ Hz}$)	± 30	
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	1.6	A
		- Continuous ($T_C = 100^\circ\text{C}$)	1.0	
I_{DM}	Drain Current	- Pulsed	(Note 1)	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	mJ
I_{AR}	Avalanche Current		(Note 1)	A
E_{AR}	Repetitive Avalanche Energy		(Note 1)	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt		(Note 3)	
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	27.8	W
		- Derate Above 25°C	0.22	$\text{W}/^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FCU4300N80Z	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	4.5	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	100	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCU4300N80Z	FCU430080Z	IPAK	Tube	N/A	N/A	75 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_D = 1 \text{ mA}$, $T_J = 25^\circ\text{C}$	800	-	-	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 1 \text{ mA}$, Referenced to 25°C	-	0.85	-	$^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 800 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$	-	-	25	μA
		$V_{\text{DS}} = 640 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $T_C = 125^\circ\text{C}$	-	-	250	
I_{GSS}	Gate to Body Leakage Current	$V_{\text{GS}} = \pm 20 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$	-	-	± 10	μA

On Characteristics

$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}} = V_{\text{DS}}$, $I_D = 0.16 \text{ mA}$	2.5	-	4.5	V
$R_{\text{DS(on)}}$	Static Drain to Source On Resistance	$V_{\text{GS}} = 10 \text{ V}$, $I_D = 0.8 \text{ A}$	-	3.4	4.3	Ω
g_{FS}	Forward Transconductance	$V_{\text{DS}} = 20 \text{ V}$, $I_D = 0.8 \text{ A}$	-	0.52	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{\text{DS}} = 100 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	267	355	pF
C_{oss}	Output Capacitance	$V_{\text{DS}} = 100 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	12	16	pF
C_{rss}	Reverse Transfer Capacitance	$V_{\text{DS}} = 100 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	0.78	-	pF
C_{oss}	Output Capacitance	$V_{\text{DS}} = 480 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	6.2	-	pF
$C_{\text{oss(eff.)}}$	Effective Output Capacitance	$V_{\text{DS}} = 0 \text{ V}$ to 480 V , $V_{\text{GS}} = 0 \text{ V}$	-	36	-	pF
$Q_{\text{g(tot)}}$	Total Gate Charge at 10V	$V_{\text{DS}} = 640 \text{ V}$, $I_D = 1.6 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$	-	6.8	8.8	nC
Q_{gs}	Gate to Source Gate Charge	$V_{\text{DS}} = 640 \text{ V}$, $I_D = 1.6 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$	(Note 4)	1.38	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	$V_{\text{DS}} = 640 \text{ V}$, $I_D = 1.6 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$		3.0	-	nC
ESR	Equivalent Series Resistance	$f = 1 \text{ MHz}$	-	2.9	-	Ω

Switching Characteristics

$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = 400 \text{ V}$, $I_D = 1.6 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$, $R_g = 4.7 \Omega$	-	10	30	ns
t_r	Turn-On Rise Time	$V_{\text{DD}} = 400 \text{ V}$, $I_D = 1.6 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$, $R_g = 4.7 \Omega$	-	6.5	23	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time	$V_{\text{DD}} = 400 \text{ V}$, $I_D = 1.6 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$, $R_g = 4.7 \Omega$	-	21	52	ns
t_f	Turn-Off Fall Time	$V_{\text{DD}} = 400 \text{ V}$, $I_D = 1.6 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$, $R_g = 4.7 \Omega$	(Note 4)	16	42	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	1.6	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	3.2	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_{\text{SD}} = 1.6 \text{ A}$	-	-	V	
t_{rr}	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}$, $I_{\text{SD}} = 1.6 \text{ A}$, $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	209	-	ns
Q_{rr}	Reverse Recovery Charge	$V_{\text{GS}} = 0 \text{ V}$, $I_{\text{SD}} = 1.6 \text{ A}$, $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	1.2	-	μC

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. $I_{\text{AS}} = 0.32 \text{ A}$, $R_g = 25 \Omega$, starting $T_J = 25^\circ\text{C}$
3. $I_{\text{SD}} \le 1.6 \text{ A}$, $dI/dt \le 200 \text{ A}/\mu\text{s}$, $V_{\text{DD}} \le \text{BV}_{\text{DSS}}$, starting $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature typical characteristic.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

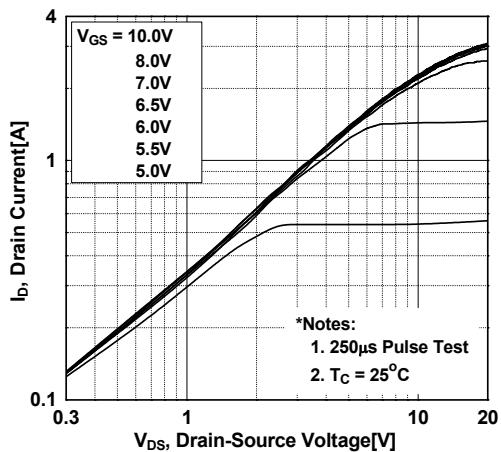


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

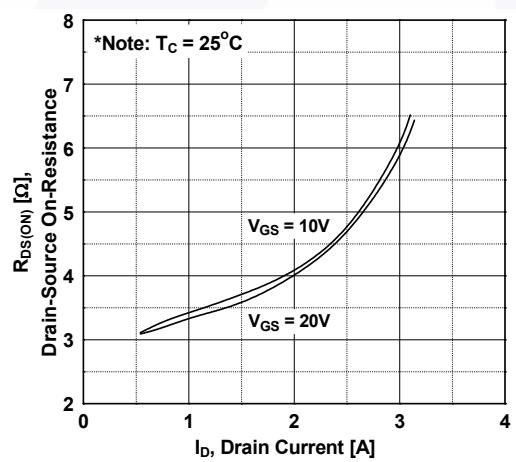


Figure 5. Capacitance Characteristics

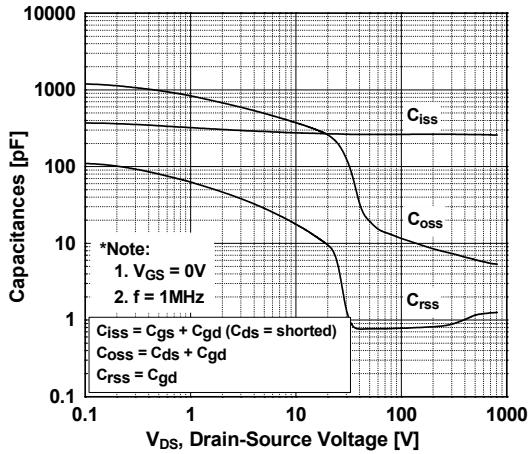


Figure 2. Transfer Characteristics

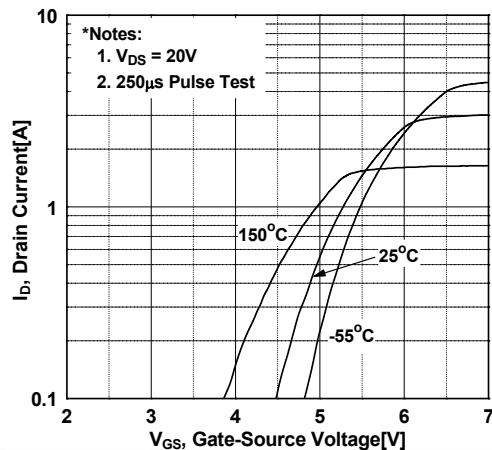


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

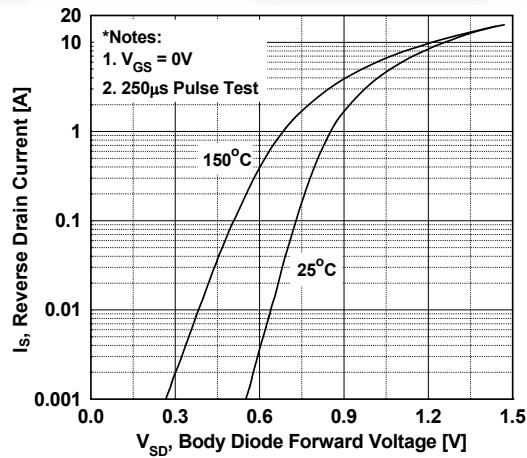
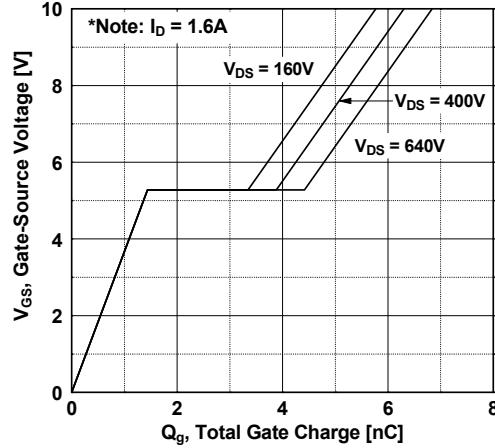


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

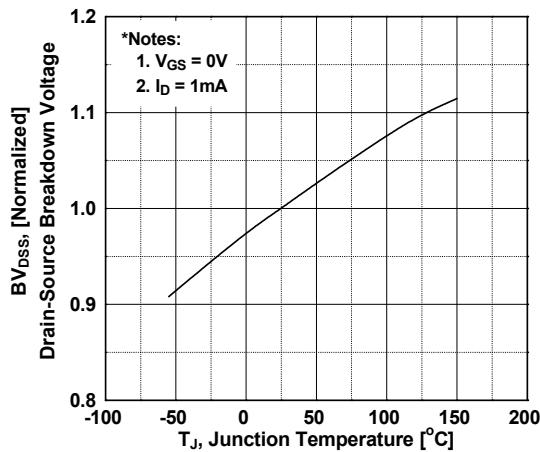


Figure 8. On-Resistance Variation vs. Temperature

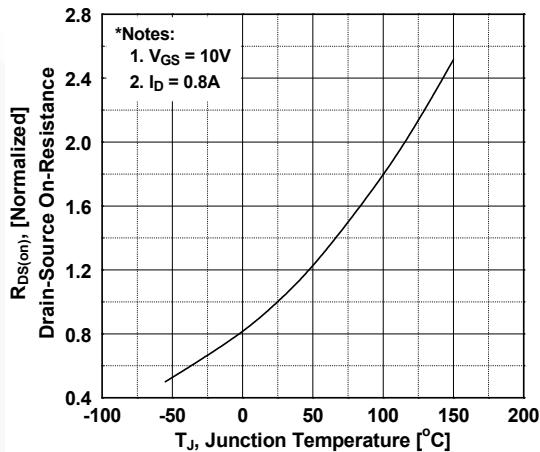


Figure 9. Maximum Safe Operating Area

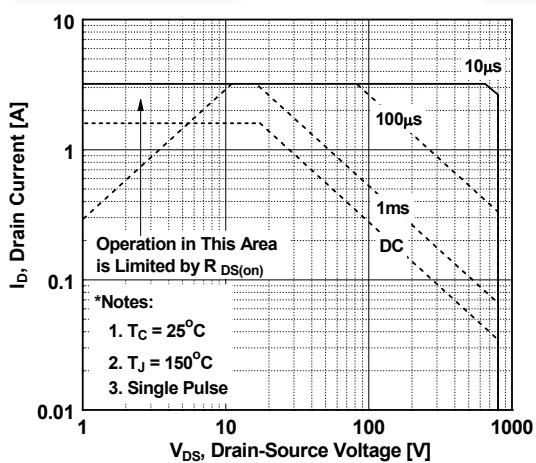


Figure 10. Maximum Drain Current vs. Case Temperature

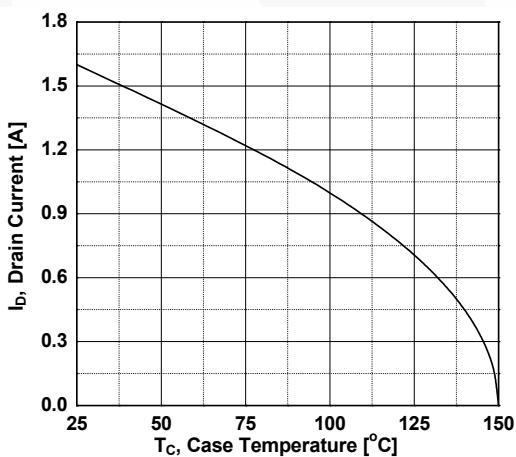
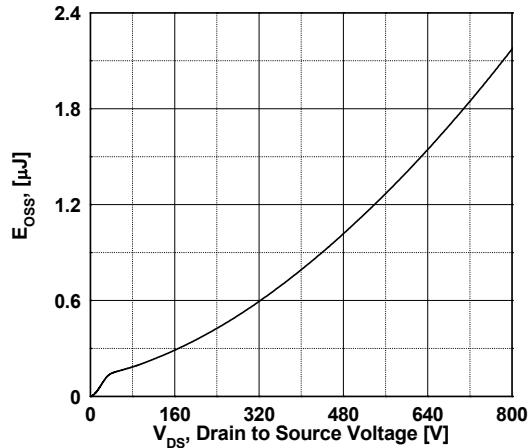
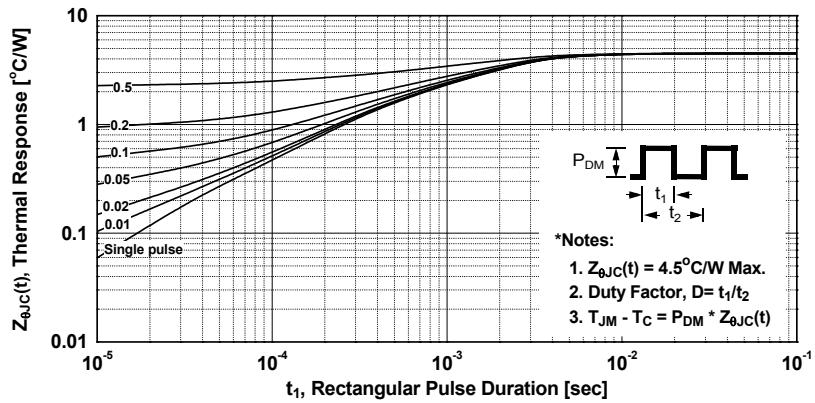


Figure 11. E_{oss} vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



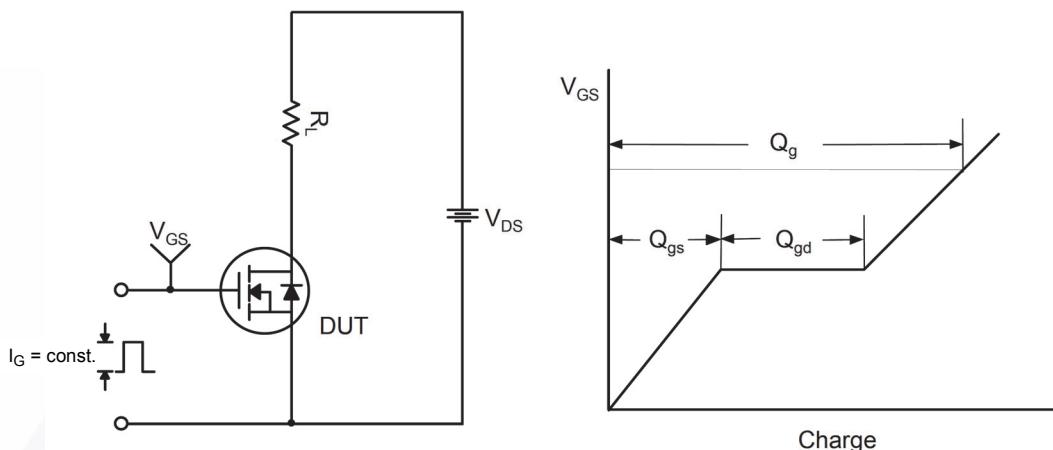


Figure 13. Gate Charge Test Circuit & Waveform

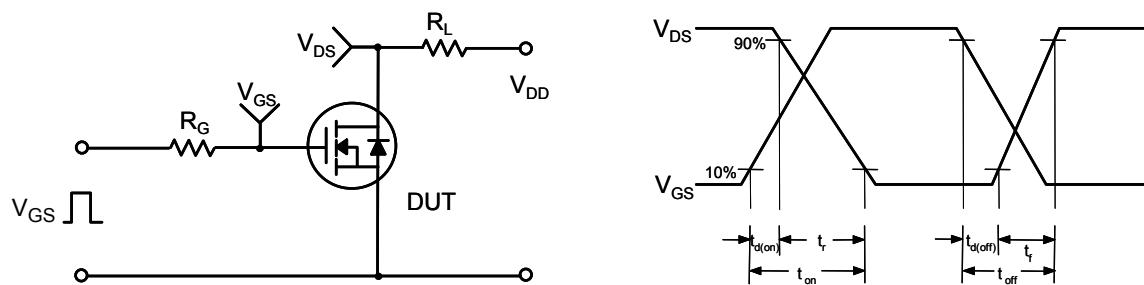


Figure 14. Resistive Switching Test Circuit & Waveforms

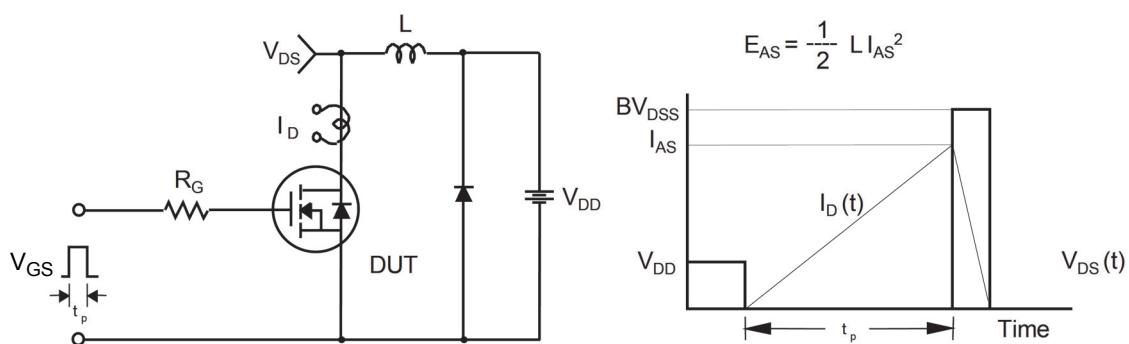


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

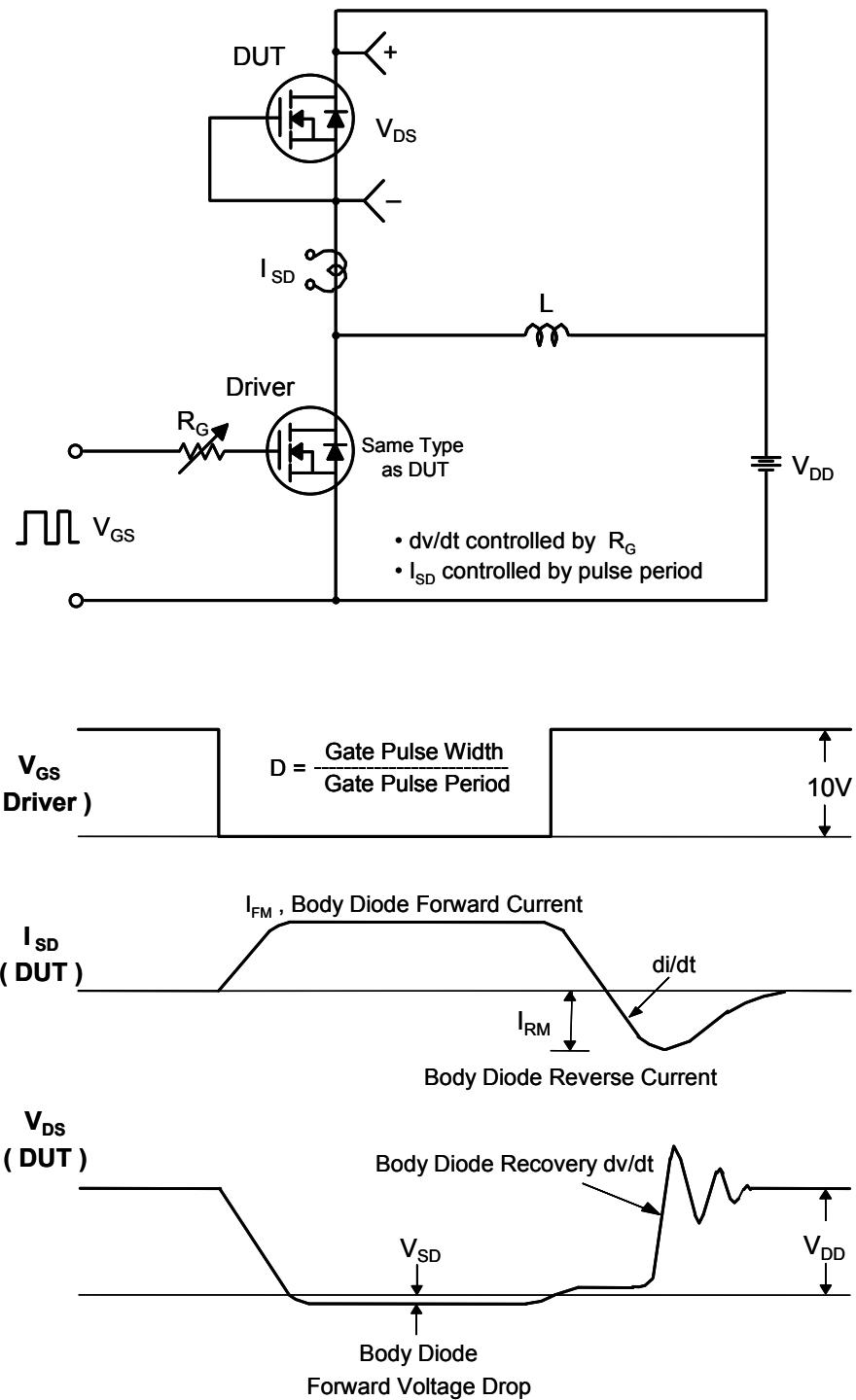
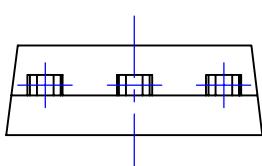
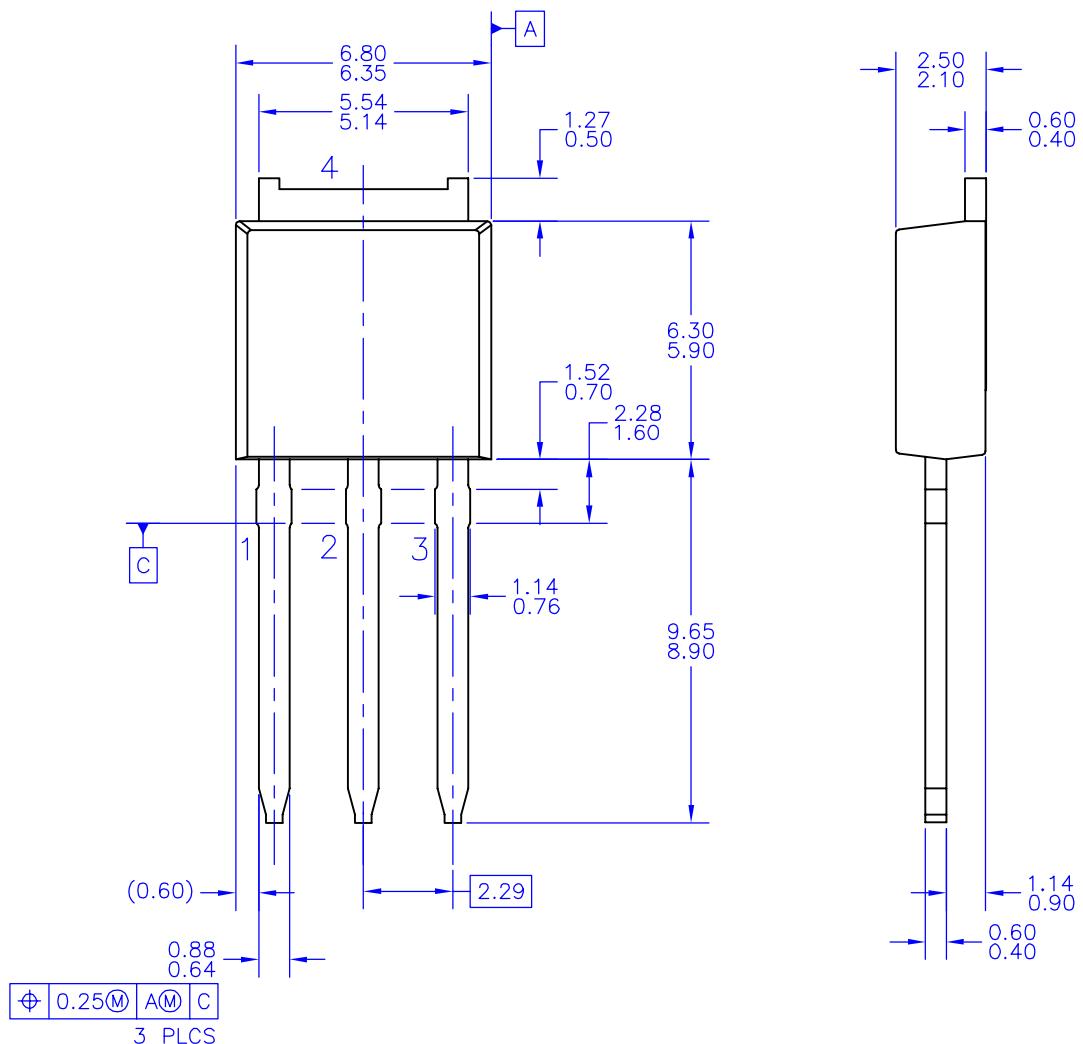


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

REVISIONS				
ltr	DESCRIPTION	E.C.N.	DATE	BY/APP'D
A	RELEASE TO DOCUMENT CONTROL	CB/031/01	16MAR2001	RM



NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) THIS PACKAGE CONFORMS TO JEDEC, TO-251, ISSUE C, VARIATION AA, DATED SEP 1988.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

APPROVALS	DATE	FAIRCHILD SEMICONDUCTOR™	CEBU PHILIPPINES
DRAWN: J. GOMEZ	16MAR2001		
CHECKED: R. MANABIT			
APPROVED: M. GESTOLE		TO-251 (I-PAK) MOLDED, 3 LEAD, OPTION AA	
G.S. BAJE			
PROJECTION	SCALE 8:1	SIZE A3	DRAWING NUMBER MKT-T0251A03
	INCH MM		REV A
		FORMERLY: N/A	SHEET : 1 OF 1



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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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